

2MBI450U4N-170-50

IGBT Modules

IGBT MODULE (U series) 1700V / 450A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

tems		Symbols	Conditions		Maximum ratings	Units
Collector-Emitter voltage		Vces			1700	V
Gate-Emitter voltage		V _{GES}			±20	V
Collector current		Ic	Continuous	Tc=25°C	600	
				Tc=80°C	450	
		Icp	1ms	Tc=25°C	1200	۸
				Tc=80°C	900	Α
		-lc			450	
		-lc pulse	1ms		900	
Collector power dissipation		Pc	1 device		2080	W
Junction temperature		Tj			150	°C
Storage temperature		Tstg			-40 to +125	C
Isolation voltage	between terminal and copper base (*1)	V	A.C. dania		2400	\/A.C
	between thermistor and others (*2)	Viso	AC : 1min.		3400	VAC
Screw torque	Mounting (*3)				3.5	NI
	Terminals (*4)	1-			4.5	N m

Note *1: All terminals should be connected together when isolation test will be done.

Note *2: Two thermistor terminals should be connected together, each other terminals should be connected together and shorted to base plate when isolation test will be done.

Note *3: Recommendable value : Mounting : 2.5-3.5 Nm (M5) Note *4: Recommendable value : Terminals : 3.5-4.5 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items		Symbols	Canditions		Characteristics			Units
ne	IIIS	Syllibols	Conditions		min.	typ.	max.	Units
	Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1700V		-	-	3.0	mA
Inverter	Gate-Emitter leakage current	I _{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		-	-	600	nA
	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 450mA		4.5	6.5	8.5	V
	Collector-Emitter saturation voltage	V _{CE (sat)}		Tj=25°C	-	2.80	3.05	V
		(terminal)) V _{GE} = 15V I _C = 450A	Tj=125°C	-	3.20	-	
		V _{CE (sat)}		Tj=25°C	-	2.25	2.45	
		(chip)		Tj=125°C	-	2.65	-	
	Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	42	-	nF
	Turn-on time	ton	V - 000V		-	0.62	1.20	
		tr	- V _{cc} = 900V - I _c = 450A	-	0.39	0.60	μs	
		tr (i)	V _{GE} = ±15V	-	0.05	-		
	Turn-off time	toff	$R_{\rm G} = 1.1\Omega$	-	0.55	1.50		
		tf	NG - 1.112	-	0.09	0.30		
	Forward on voltage	VF		Tj=25°C	-	2.25	2.55	
		(terminal)	V _{GE} = 0V I _F = 450A	Tj=125°C	-	2.45	-	V
		VF		Tj=25°C	-	1.80	1.95	
		(chip)		Tj=125°C	-	2.00	-	
	Reverse recovery time	trr	I _F = 450A		-	0.18	0.6	μs
	Lead resistance, terminal-chip (*5)	R lead			-	1.00	-	mΩ
Thermistor	Resistance	R	T=25°C		-	5000	-	Ω
	Resistance		T=100°C		465	495	520	
Ĕ	B value	В	T=25/50°C	·	3305	3375	3450	K

Note *5: Biggest internal terminal resistance among arm.

● Thermal resistance characteristics

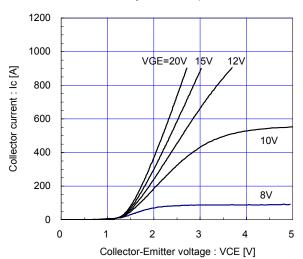
Items	Symbols	Conditions	Characteristics			Units
itellis		Conditions	min.	typ.	max.	Ullits
Thermal resistance (1device)	Rth(j-c)	IGBT	-	-	0.06	°C/W
mermanesistance (ruevice)		FWD	-	-	0.10	
Contact thermal resistance (1device) (*6)	Rth(c-f)	with Thermal Compound	-	0.0167	-	

Note *6: This is the value which is defined mounting on the additional cooling fin with thermal compound.

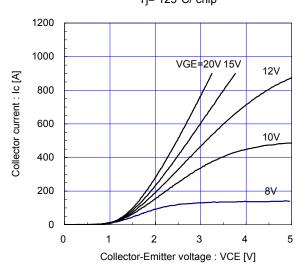
■ Characteristics (Representative)

Collector current vs. Collector-Emitter voltage (typ.)

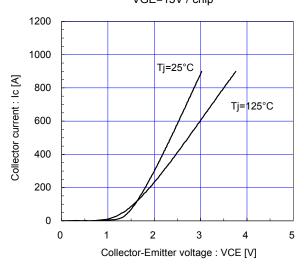
Tj= 25°C / chip



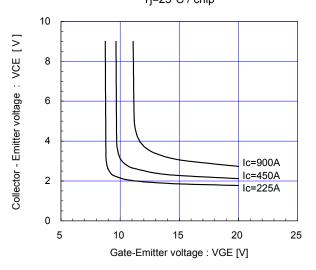
Collector current vs. Collector-Emitter voltage (typ.) $Tj=125^{\circ}C/chip$



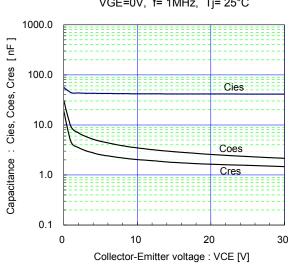
Collector current vs. Collector-Emitter voltage (typ.) VGE=15V / chip



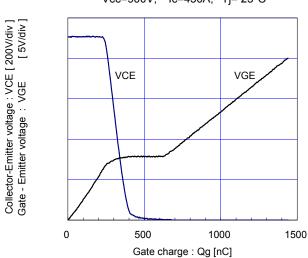
Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj=25°C / chip

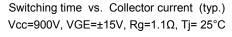


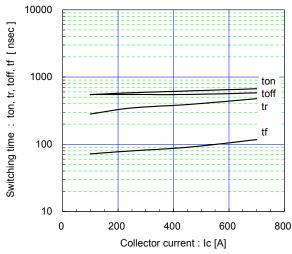
Capacitance vs. Collector-Emitter voltage (typ.) VGE=0V, f= 1MHz, Tj= 25°C



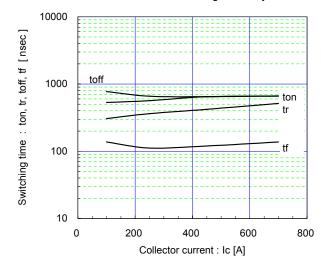
Dynamic Gate charge (typ.) Vcc=900V, Ic=450A, Tj= 25°C



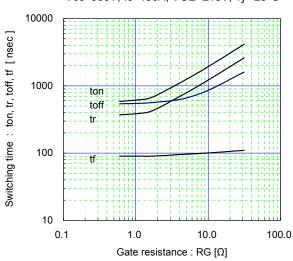




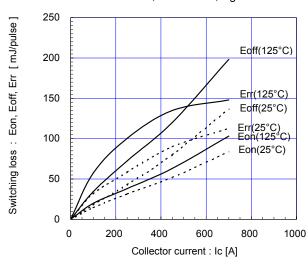
Switching time vs. Collector current (typ.) Vcc=900V, $VGE=\pm15V$, $Rg=1.1\Omega$, $Tj=125^{\circ}C$



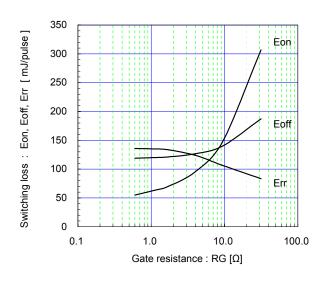
Switching time vs. Gate resistance (typ.) Vcc=900V, Ic=450A, VGE=±15V, Tj= 25°C



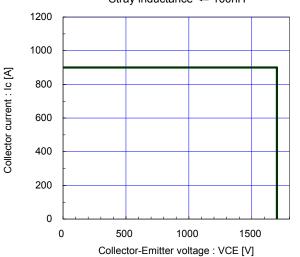
Switching loss vs. Collector current (typ.) Vcc=900V, $VGE=\pm15V$, $Rg=1.1\Omega$



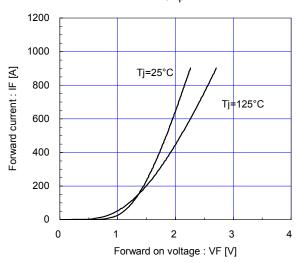
Switching loss vs. Gate resistance (typ.) Vcc=900V, Ic=450A, VGE=±15V, Tj= 125°C



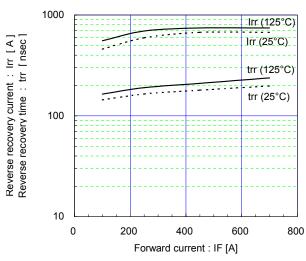
Reverse bias safe operating area (max.) +VGE=15V,-VGE <= 15V, RG >= 1.1Ω , Tj <= 125° C Stray inductance <= 100nH



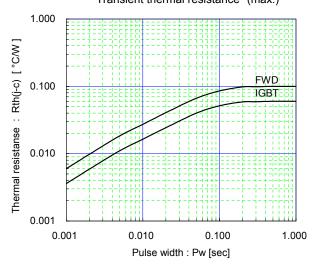
Forward current vs. Forward on voltage (typ.) chip



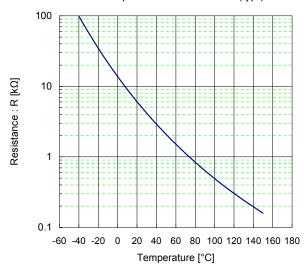
Reverse recovery characteristics (typ.) Vcc=900V, VGE= \pm 15V, Rg=1.1 Ω



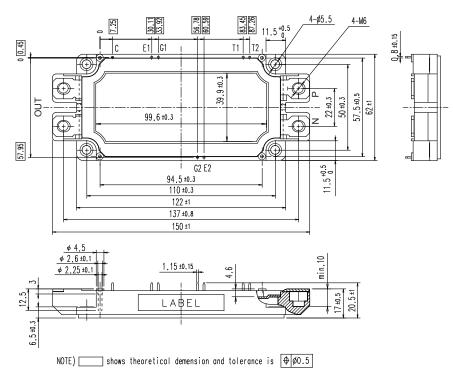
Transient thermal resistance (max.)



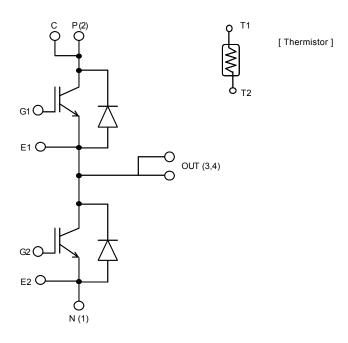
[Thermistor]
Temperature characteristic (typ.)



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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